



50V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _C = +25°C
50V	13mΩ @ V _{GS} = 10V	51.4A
50 V	$20m\Omega$ @ V _{GS} = 4.5V	41.7A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

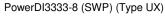
Features

- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- Low On-Resistance
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

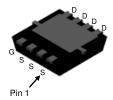
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.072 grams (Approximate)

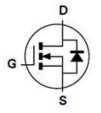






Top View

Bottom View



Equivalent Circuit

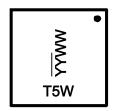
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT5012LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2000/Tape & Reel
DMT5012LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



T5W = Product Type Marking Code YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 20 = 2020)

WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	50	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Dunin Courset (Note 5) // 40//	$T_C = +25$ °C $T_C = +70$ °C	ID	51.4 41.1	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	11.7 9.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	205	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	ls	51	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 19	I _{SM}	205	Α	
Avalanche Current, L = 0.1mH	las	23.2	А	
Avalanche Energy, L = 0.1mH	Eas	26.9	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W	
Total Power Dissipation (Note 6)	PD	51.4	W	
Thermal Resistance, Junction to Case (Note 6)	RеJC	2.43	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

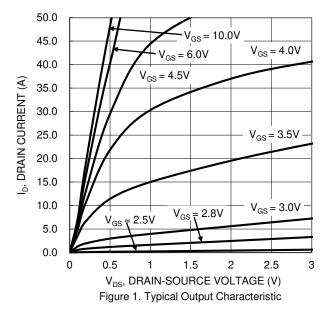
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	50	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	$V_{DS} = 40V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.2	_	2.3	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	9.2	13	mO	$V_{GS} = 10V, I_D = 10A$	
Static Drain-Source On-Nesistance	RDS(ON)	_	14.3	20	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	VsD	_	0.7	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	738	_	рF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	_	279	_	рF	V _{DS} = 30V, V _{GS} = 0V, - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	23	_	pF	1 = 1101112	
Gate Resistance	Rg	_	1.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	10.5	_	nC		
Total Gate Charge (VGS = 10V)	Qg	_	17.6	_	nC	V 20V I- 10A	
Gate-Source Charge	Qgs	_	3.5	_	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Qgd	_	5.0	_	nC	1	
Turn-On Delay Time	tD(ON)	_	7.7	_	ns		
Turn-On Rise Time	t _R	_	2.9	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 6\Omega, I_D = 10A$	
Turn-Off Delay Time	tD(OFF)	_	16.9	_	ns		
Turn-Off Fall Time	tr	_	10.2	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	40.2	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	56.9	_	nC	IF = 10A, di/dt = 300A/μs	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





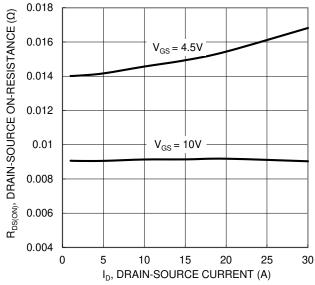


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

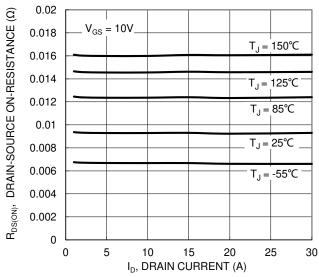


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

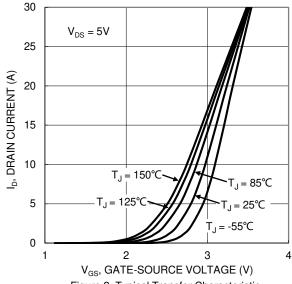


Figure 2. Typical Transfer Characteristic

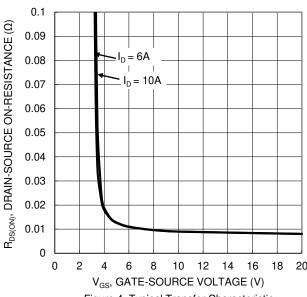


Figure 4. Typical Transfer Characteristic

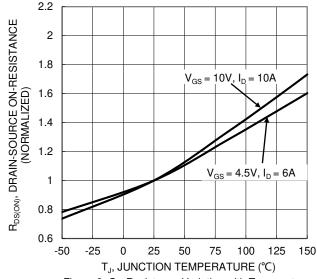


Figure 6. On-Resistance Variation with Temperature



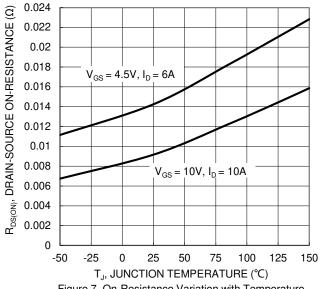


Figure 7. On-Resistance Variation with Temperature

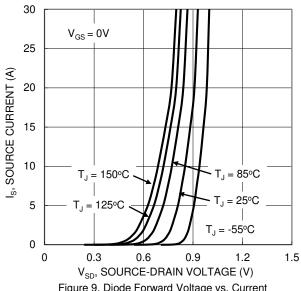


Figure 9. Diode Forward Voltage vs. Current

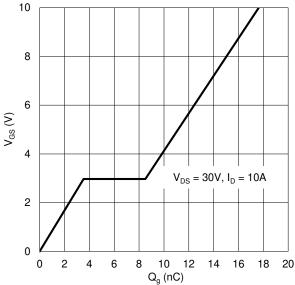


Figure 11. Gate Charge

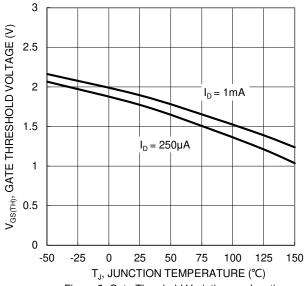


Figure 8. Gate Threshold Variation vs. Junction Temperature

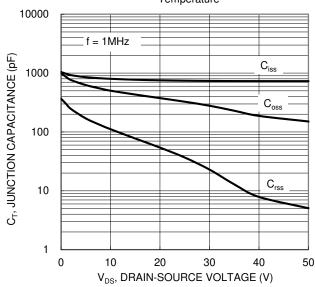


Figure 10. Typical Junction Capacitance

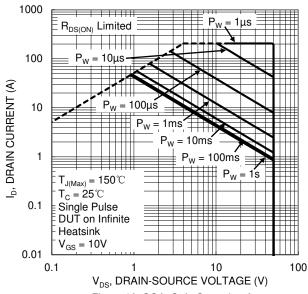


Figure 12. SOA, Safe Operation Area



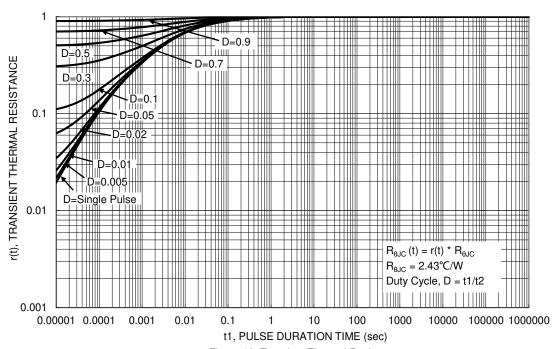


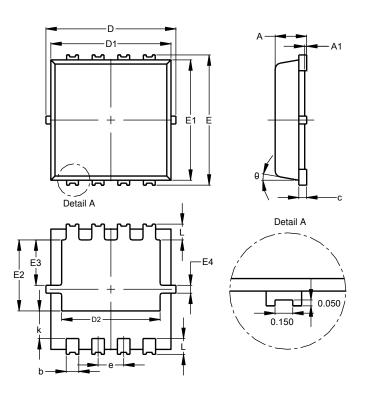
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

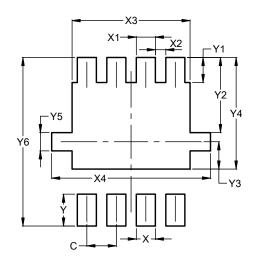


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Max Typ			
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
E	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.600		
X4	3.500		
Υ	0.700		
Y1	0.550		
Y2	1.650		
Y3	0.600		
Y4	2.450		
Y5	0.400		
Y6	3.700		



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